



10/609,157

In the United States Patent and Trademark Office

Serial Number: NA

10/609,157

Appn. Filed: 06/30/2003 (by returned receiving postcard)

Applicant: Hai Jiang

Appn. Title: FABRICATION OF ULTRA-SMALL MEMORY ELEMENTS

Mailed: 09/16/2003

At: Fremont, CA 94539

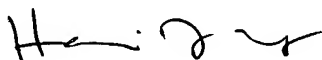
Information Disclosure Statement

Commissioner for Patent
Washington, DC 20231

Sir:

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Very respectfully,

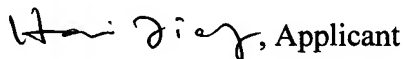
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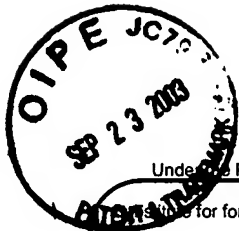
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PTO/SB/08B (04-03)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete if Known

Application Number	
Filing Date	06-30-2003
First Named Inventor	Hai Jiang
Art Unit	
Examiner Name	
Attorney Docket Number	

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Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	F	J. N. Zhou, etc, "Thickness dependence of magnetic percolation threshold in as-deposited	
		and annealed Fe-SiO ₂ granular very thin films", J. Appl. Phys. 84, (1998)5693	
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		alone and embedded applications", http://www.intel.com/research/silicon/flash.htm	

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